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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: 7/15/03

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Sheet | 1 | of | 1

Complete if Known	
Application Number	09/927,648
Filing Date	08/13/2001
First Named Inventor	Thomas H. Lee
Group Art Unit	2818
Examiner Name	Howard Weiss
Attorney Docket Number	035905-0104

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document Number	U.S. Patent Document Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	C9	5,999,453		Kawata	12/7/99	
	C10	5,739,567		Wong	4/14/98	
	C11	4,774,556		Fujii et al	9/27/88	
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	C17		WO 00/30118		Johnson, et al	5/25/00		Y

NON PATENT LITERATURE DOCUMENTS

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	A51	5,427,979		Chang	6/27/1995	
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Attorney Docket Number	035905/0104

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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First Named Inventor	Thomas H. Lee et al.
Group Art Unit	2818
Examiner Name	Unassigned
Attorney Docket Number	035905/0104

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[6]
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Examiner Signature		Date Considered	10/3/03

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Date Submitted: June 11, 2002

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Sheet 1 of 7

Complete if Known	
Application Number	09/927,648
Filing Date	08/13/2001
First Named Inventor	Thomas H. LEE et al.
Group Art Unit	2818
Examiner Name	Unassigned
Attorney Docket Number	035905-0104

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	U.S. Patent Document: Number	Kind Code[2] (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	B1	4,500,905		Shibata		
	B2	6,185,122		Johnson et al.		
	B3	3,414,892		McCormack et al.	12/13/1968	
	B4	3,432,827		Sarno	3/11/1969	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	09/927,648
				Filing Date	08/13/2001
Date Submitted: June 11, 2002				First Named Inventor	Thomas H. LEE et al.
				Group Art Unit	2818
(use as many sheets as necessary)				Examiner Name	Unassigned
Sheet	2	of	7	Attorney Docket Number	035905-0104

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	B57	6,353,265	B1	Michii		
	B58	6,355,501	B1	Fung et al.		
	B59	6,197,641	B1	Hergenrother et al.		

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Examiner Initials*	Cite No.[1]	Foreign Patent Document Office[3]	Number[4]	Kind Code[5] (if known)	Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
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Sheet 3 of 7

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Application Number	09/927,648
Filing Date	08/13/2001
First Named Inventor	Thomas H. LEE et al.
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Sheet 4 of 7

Complete if Known	
Application Number	09/927,648
Filing Date	08/13/2001
First Named Inventor	Thomas H. LEE et al.
Group Art Unit	2818
Examiner Name	Unassigned
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Sheet 5 of 7

Complete if Known	
Application Number	09/927,648
Filing Date	08/13/2001
First Named Inventor	Thomas H. LEE et al.
Group Art Unit	2818
Examiner Name	Unassigned
Attorney Docket Number	035905-0104

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Examiner Signature		Date Considered	10/3/03

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	Application Number	09/927,648
	Filing Date	08/13/2001
	First Named Invent r	Thomas H. LEE et al.
	Group Art Unit	2818
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Sheet 7 of 7

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	B120	Patent Application, AKRAM, US 2002/0030263 A1.	
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[1] Unique citation designation number. [2] See attached Kinds of U.S. Patent Documents. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached.

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